Quad buffer (3-State) 74ABT126

FEATURES

- Quad bus interface
- 3-State buffers
- Output capability: +64mA/-32mA
- Latch-up protection exceeds 500mA per Jedec JC40.2 Std 17
- ESD protection exceeds 2000 V per MIL STD 883C Method 3015.6 and 200 V per Machine Model

DESCRIPTION

The 74ABT126 high-performance BiCMOS device combines low static and dynamic power dissipation with high speed and high output drive.

The 74ABT126 device is an quad buffer that is ideal for driving bus lines. The device features four Output Enables (OE0, OE1, OE2, OE3), each controlling one of the 3-State outputs.

FUNCTION TABLE

INPUTS		OUTPUT
OEn	Dn	Qn
H	L	L
H	H	H
L	X	Z

H = High voltage level
L = Low voltage level
X = Don't care
Z = High impedance "off" state

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS T_{amb} = 25°C; GND = 0V	TYPICAL	UNIT
t_{PLH} t_{PHL}	Propagation delay An to Yn	C_L = 50pF; V_{CC} = 5V	2.9	ns
C_{IN}	Input capacitance	V_I = 0V or V_{CC}	4	pF
C_{OUT}	Output capacitance	V_I = 0V or V_{CC}	7	pF
I_{CCZ}	Total supply current	Outputs Disabled; V_{CC} = 5.5V	500	nA

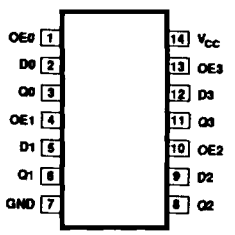
ORDERING INFORMATION

PACKAGES	TEMPERATURE RANGE	ORDER CODE
14-pin plastic DIP	-40°C to +85°C	74ABT126N
14-pin plastic SOL	-40°C to +85°C	74ABT126D

PIN DESCRIPTION

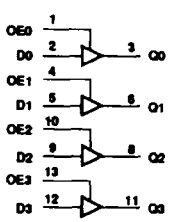
PIN NUMBER	SYMBOL	FUNCTION
2, 5, 9, 12	D0 - D3	Data inputs
3, 6, 8, 11	Q0 - Q3	Data outputs
1, 4, 10, 13	OE0 - OE3	Data outputs
7	GND	Ground (0V)
14	V_{CC}	Positive supply voltage

PIN CONFIGURATION

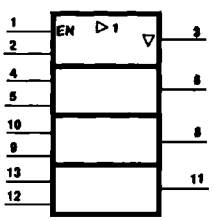


Top view

LOGIC SYMBOL



LOGIC SYMBOL (IEEE/IEC)



ABSOLUTE MAXIMUM RATINGS[1, 2]

SYMBOL	PARAMETER	CONDITIONS	RATING	UNIT
V_{CC}	DC supply voltage		-0.5 to +7.0	V
I_{IK}	DC input diode current	$V_I < 0$	-18	mA
V_I	DC input voltage[3]		-1.2 to +7.0	V
I_{OK}	DC output diode current	$V_O < 0$	-50	mA
V_{OUT}	DC output voltage[3]	output in Off or High state	-0.5 to +5.5	V
I_{OUT}	DC output current	output in Low state	128	mA
T_{stg}	Storage temperature range		-65 to 150	°C

NOTES:
1. Stresses beyond those listed may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
2. The performance capability of a high-performance integrated circuit in conjunction with its thermal environment can create junction temperatures which are detrimental to reliability. The maximum junction temperature of this integrated circuit should not exceed 150°C.
3. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	LIMITS		UNIT
		Min	Max	
V_{CC}	DC supply voltage	4.5	5.5	V
V_I	Input voltage	0	V_{CC}	V
V_{IH}	High-level input voltage	2.0		V
V_{IL}	Input voltage		0.8	V
I_{OH}	High level output current		-32	mA
I_{OL}	Low level output current		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	0	5	ns/V
T_{amb}	Operating free-air temperature range	-40	+85	°C

DC ELECTRICAL CHARACTERISTICS

SYMBOL	PARAMETER	TEST CONDITIONS	LIMITS					UNIT
			T_{amb} = +25°C			T_{amb} = -40°C to +85°C		
			Min	Typ	Max	Min	Max	
V_{IK}	Input clamp voltage	V_{CC} = 4.5V; I_{IK} = -18mA		-0.9	-1.2		-1.2	V
V_{OH}	High-level output voltage	V_{CC} = 4.5V; I_{OH} = -3mA; V_I = V_{IL} or V_{IH}	2.5	2.9		2.5		V
		V_{CC} = 5.0V; I_{OH} = -3mA; V_I = V_{IL} or V_{IH}	3.0	3.4		3.0		
		V_{CC} = 4.5V; I_{OH} = -32mA; V_I = V_{IL} or V_{IH}	2.0	2.4		2.0		
V_{OL}	Low-level output voltage	V_{CC} = 4.5V; I_{OL} = 64mA; V_I = V_{IL} or V_{IH}		0.42	0.55		0.55	V
I_I	Input leakage current	V_{CC} = 5.5V; V_I = GND or 5.5V		±0.01	±1.0		±1.0	µA
I_{OZH}	3-State output High current	V_{CC} = 5.5V; V_O = 2.7V; V_I = V_{IL} or V_{IH}		5.0	50		50	µA
I_{OZL}	3-State output Low current	V_{CC} = 5.5V; V_O = 0.5V; V_I = V_{IL} or V_{IH}		-5.0	-50		-50	µA
I_O	Short-circuit output current[1]	V_{CC} = 5.5V; V_O = 2.5V	-50	-100	-180	-50	-180	mA
I_{CCH}	Quiescent supply current	V_{CC} = 5.5V; Outputs High; V_I = GND or V_{CC}		0.5	50		50	µA
I_{CCL}		V_{CC} = 5.5V; Outputs Low; V_I = GND or V_{CC}		24	30		30	mA
I_{CCZ}		V_{CC} = 5.5V; Outputs 3-State; V_I = GND or V_{CC}		0.5	50		50	µA
ΔI_{CC}	Additional supply current per input pin[2]	Outputs enabled, one input at 3.4V, other inputs at V_{CC} or GND; V_{CC} = 5.5V		0.5	1.5		1.5	mA
		Outputs 3-State, one data input at 3.4V, other inputs at V_{CC} or GND; V_{CC} = 5.5V		0.5	50		50	µA
		Outputs 3-State, one enable input at 3.4V, other inputs at V_{CC} or GND; V_{CC} = 5.5V		0.5	1.5		1.5	mA

NOTES:

1. Not more than one output should be tested at a time, and the duration of the test should not exceed one second.
2. This is the increase in supply current for each input at 3.4V.